

200-V half-bridge driver with shutdown and V_{CC} & V_{BS} UVLO

Features

- Gate drive supplies up to 20 V per channel
- Undervoltage lockout for V_{CC}, V_{BS}
- 3.3 V, 5 V, 15 V input logic compatible
- Tolerant to negative transient voltage
- Designed for use with bootstrap power supplies
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- Internal set deadtime
- High-side output in phase with input
- Shutdown input turns off both channels
- -40°C to 125°C operating range
- RoHS compliant

Product Summary

Voffset	≤ 200V
V _{оит}	10 V – 20 V
I _{o+} & I _{o-} (typ.)	290 mA & 600 mA
ton & toff (typ.)	680 ns & 150 ns
Deadtime (typ.)	520 ns

Description

The IRS2008 is a high voltage, high speed power MOSFET and IGBT driver with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3 V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver crossconduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 200 V. Propagation delays are matched to simplify the HVIC's use in high frequency applications.

Package Options



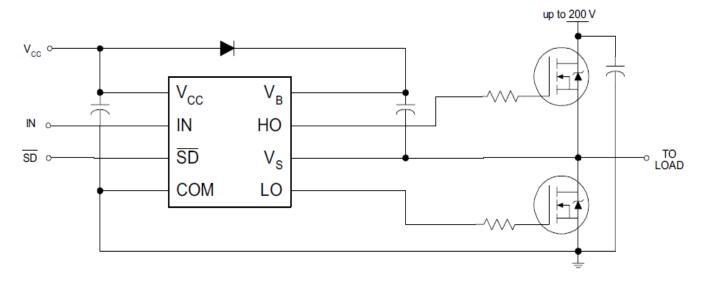
Typical Applications

- Appliance motor drives, Stepper motor, Servo drives
- · Micro inverter drives
- General purpose three phase inverters
- Light electric vehicles (e-bikes, e-scooters, e-toys)
- Wireless Charging
- General battery driven applications

Door Don't Normalism	Daalaana Tama	Standard Pack				Onderskie Bert Neusker
Base Part Number	Package Type	Form	Quantity	Orderable Part Number		
		Tape and Reel	2500	IRS2008STRPBF		
IRS2008S	8-Lead SOIC	Tube/Bulk	95	IRS2008SPBF		
<u>IRS2008M</u>	14-Lead MLPQ 4x4	Tape and Reel	3000	IRS2008MTRPBF		



Typical Connection Diagram



(Refer to Lead Assignments for correct pin configuration). This diagram shows electrical connections only. Please refer tour Application Notes & DesignTips for proper circuit board layout.



Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM unless otherwise stated in the table. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Definition		Max.	Units
Vcc	Low side supply voltage		-0.3	25 [†]	
V _{IN}	Logic input voltage (IN & S	D)	COM - 0.3	V _{CC} + 0.3	
V _B	High-side floating well supp	oly voltage	-0.3	225	
Vs	High-side floating well supp	oly return voltage	V _B - 25	V _B + 0.3	V
V _{HO}	Floating gate drive output v	/oltage	Vs - 0.3	V _B + 0.3	
V _{LO}	Low-side output voltage	Low-side output voltage		Vcc + 0.3	
COM	Power ground		V _{CC} - 25	V _{CC} + 0.3	
dVs/dt	Allowable V _S offset supply	transient relative to COM	_	50	V/ns
Б	Package power	8-Lead SOIC	_	0.625	W
P_D	dissipation @ T _A ≤+25°C	14-Lead MLPQ 4x4	_	2.08	¬
D4h	Thermal resistance,	8-Lead SOIC	_	200	00/14/
Rth _{JA}	junction to ambient	14-Lead MLPQ 4x4	_	36	°C/W
TJ	Junction temperature		_	150	
Ts	Storage temperature		-55	150	°C
TL	Lead temperature (solderin	ng, 10 seconds)	_	300	

† All supplies are tested at 25V.

Recommended Operating Conditions

For proper operation, the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to COM unless otherwise stated in the table. The offset rating is tested with supplies of $(V_{CC} - COM) = (V_B - V_S) = 15V$.

Symbol	Definition	Min	Max	Units
V _{CC}	Low-side supply voltage	10	20	
Vin	Logic input voltage(IN & SD)	0	Vcc	
V _B	High-side floating well supply voltage	V _S + 10	V _S + 20	
Vs	High-side floating well supply offset voltage†	COM - 8 [†]	200	7 v
Vно	Floating gate drive output voltage	Vs	V _B	
V _{LO}	Low-side output voltage	COM	Vcc	
TA	Ambient temperature	-40	125	°C

[†] Logic operation for VS of –8 V to 200 V. Logic state held for V_S of –8 V to –V_{BS}. Please refer to Design Tip DT97-3 for more details.



Static Electrical Characteristics

 $(V_{CC} - COM) = (V_B - V_S) = 15V$. $T_A = 25^{\circ}C$ unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to respective V_S and COM and are applicable to the respective output leads HO or LO. The V_{CCUV} parameters are referenced to COM. The V_{BSUV} parameters are referenced to V_S .

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{BSUV} +	V _{BS} supply undervoltage positive going threshold	8.0	8.9	9.8		
V_{BSUV}	V _{BS} supply undervoltage negative going threshold	7.4	8.2	9		
V_{BSUVHY}	V _{BS} supply undervoltage hysteresis	_	0.7	_		
V_{CCUV+}	V _{CC} supply undervoltage positive going threshold	8.0	8.9	9.8	V	
V _{CCUV} -	V _{CC} supply undervoltage negative going threshold	7.4	8.2	9		
V_{CCUVHY}	Vcc supply undervoltage hysteresis		0.7			
I_{LK}	High-side floating well offset supply leakage			50		$V_B = V_S = 200V$
I_{QBS}	Quiescent V _{BS} supply current		45	75	μΑ	All inputs are in the
I_{QCC}	Quiescent Vcc supply current	_	300	520		off state
V_{OH}	High level output voltage drop, V _{BIAS} -V _O		0.05	0.2	V	I _O = 2 mA
V_{OL}	Low level output voltage drop, Vo — 0.02 0.1		v	10 = 2 IIIA		
I _{o+}	Output high short circuit pulsed current	200	290	_	mA	Vo = 0V PW ≤ 10μs
I _{o-}	Output low short circuit pulsed current	420	600	_	IIIA	V _O = 15V PW ≤ 10μs
V_{IH}	Logic "1" (HO) & Logic "0" (LO) input voltage	2.5		_		
V_{IL}	Logic "0" (HO) & Logic "1" (LO) input voltage	_	_	0.8		
$V_{SD,TH+}$	SD input positive going threshold	2.5		_	V	Vcc=10V to 20V
$V_{SD,TH-}$	SD input negative going threshold	_	_	0.8		
I _{IN+}	Logic "1" Input bias current	_	3	10		V _{IN} = 5V
I _{IN-}	Logic "0" Input bias current	_	_	5	μA	V _{IN} = 0V

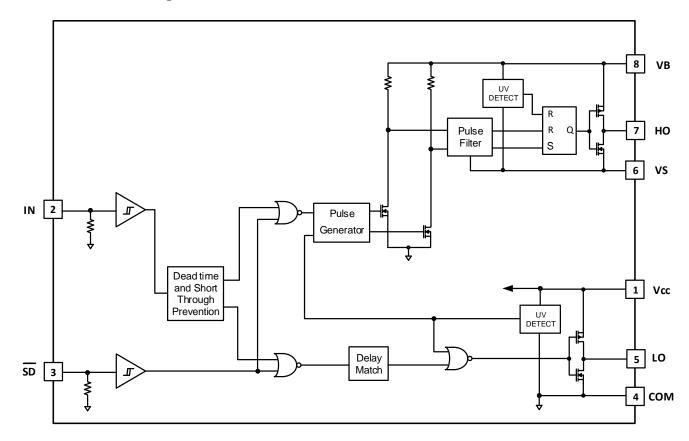
Dynamic Electrical Characteristics

 $V_{CC} = V_B = 15V$, $V_S = COM$, $T_A = 25^{\circ}C$, and $C_L = 1000 pF$ unless otherwise specified.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
ton	Turn-on propagation delay		680	870		
toff	Turn-off propagation delay	_	150	220		Vs = 0V or 200V
t _{SD}	Shutdown propagation delay	_	160	220		
t _R	Turn-on rise time	_	70	170	ns	V _S = 0V
t _F	Turn-off fall time	_	30	90		V _S = UV
DT	Deadtime, LS turn-off to HS turn-on & HS turn-on to LS turn-off	400	520	650		
MT	Delay matching time (ton, toff)	_	_	60		



Functional Block Diagram

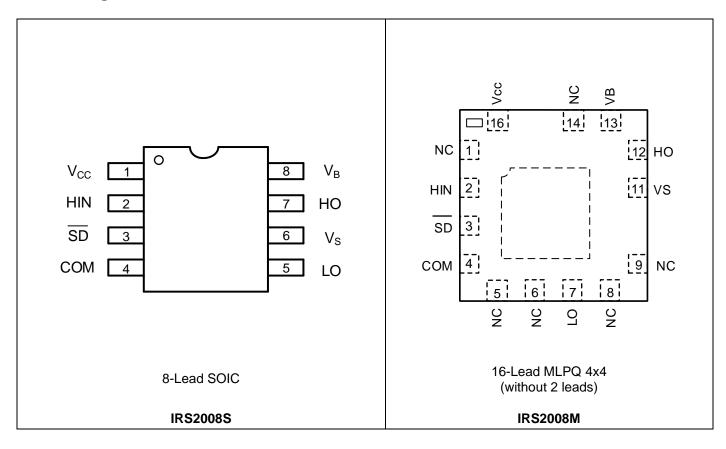




Lead Definitions

Symbol	Description
Vcc	Low-side and logic supply voltage
VB	High-side gate drive floating supply
VS	High voltage floating supply return
IN	Logic inputs for high and low side gate driver output (HO and LO), in phase with HO
SD	Logic inputs for shutdown
НО	High-side driver output
LO	Low-side driver output
COM	Low-side gate drive return

Lead Assignments





Application Information and Additional Details

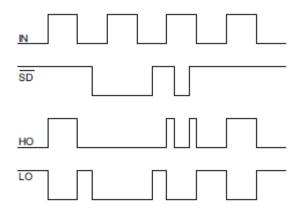


Figure 1. Input/Output Timing Diagram

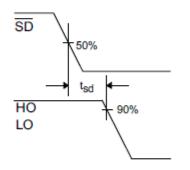


Figure 3. Shutdown Waveform Definitions

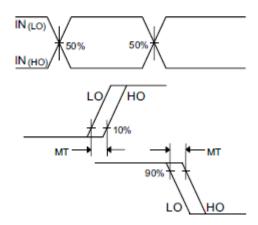


Figure 5. Delay Matching Waveform Definitions

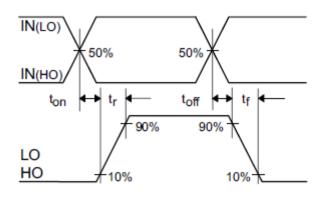


Figure 2. Switching Time Waveform Definitions

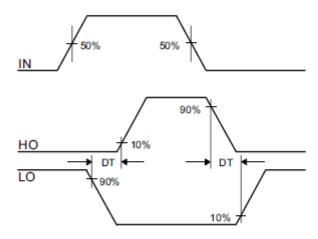


Figure 4. Deadtime Waveform Definitions

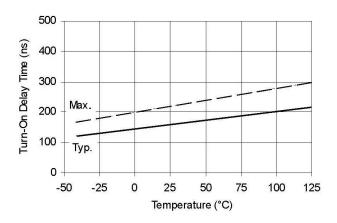


Figure 6A. Turn-On Time vs. Temperature

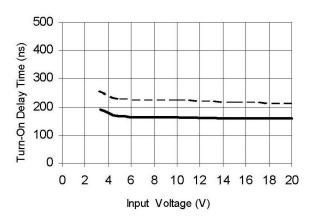


Figure 6C. Turn-On Time vs. Input Voltage

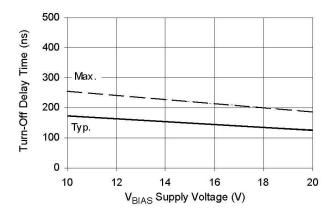


Figure 7B. Turn-Off Time vs. Supply Voltage

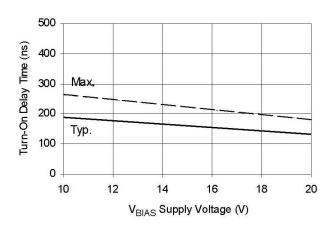


Figure 6B. Turn-On Time vs. Supply Voltage

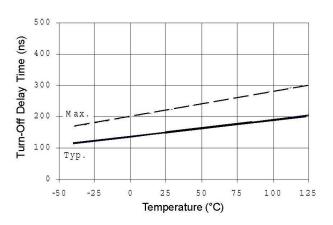


Figure 7A. Turn-Off Time vs. Temperature

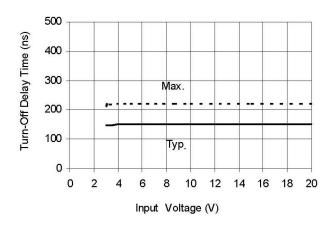


Figure 7C. Turn-Off Time vs. Input Voltage

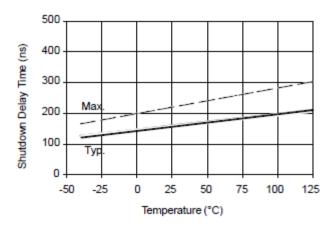


Figure 8A. Shutdown Time vs. Temperature

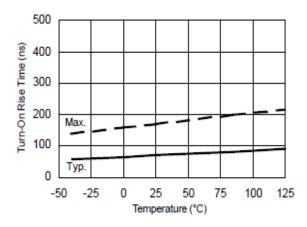


Figure 9A. Turn-On Rise Time vs. Temperature

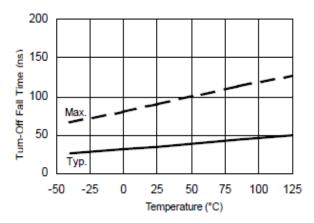


Figure 10A. Turn-Off Fall Time vs. Temperature

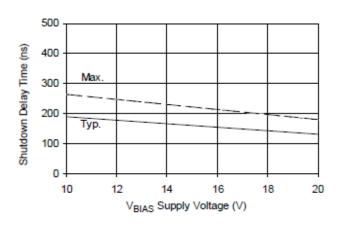


Figure 8B. Shutdown Time vs. Voltage

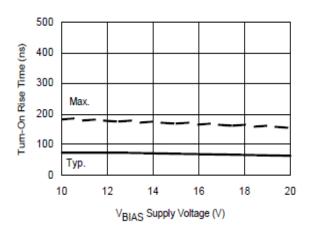


Figure 9B. Turn-On Rise Time vs. Voltage

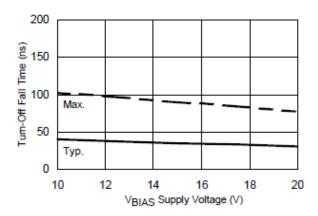


Figure 10B. Turn-Off Fall Time vs. Voltage

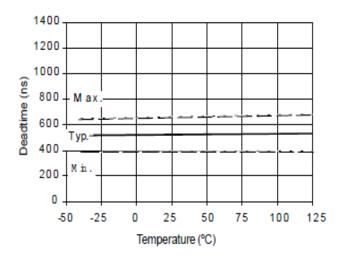


Figure 11A. Deadtime vs. Temperature

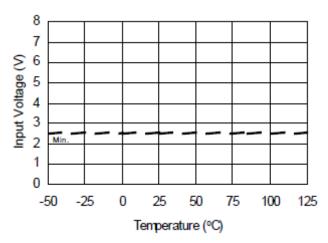


Figure 12A. Logic "1" Input Voltage vs. Temperature

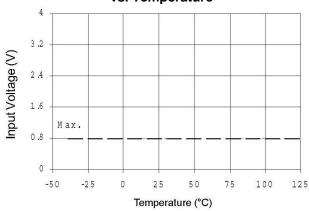


Figure 13A. Logic "0"(HO) & Logic "1"(LO) & Active SD Input Voltages vs. Temperature

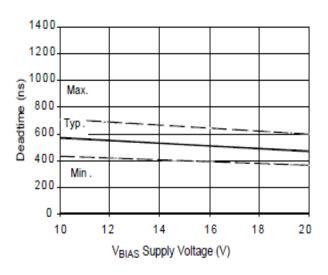


Figure 11B. Deadtime vs. Voltage

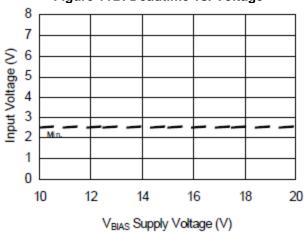


Figure 12B. Logic "1" Input Voltage vs. Voltage

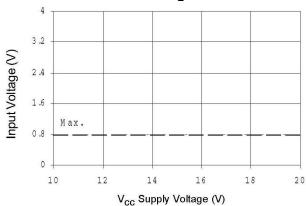


Figure 13B. Logic "0"(HO) & Logic "1"(LO) & Active SD Input Voltages vs Supply Voltage

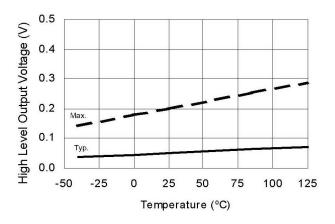


Figure 14A. High Level Output Voltage vs. Temperature

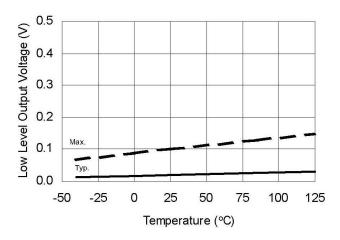


Figure 15A. Low Level Output Voltage vs. Temperature

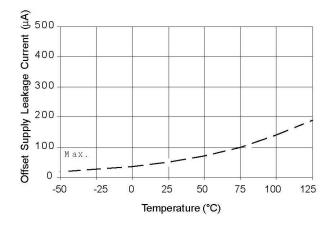


Figure 16A. Offset Supply Current vs. Temperature

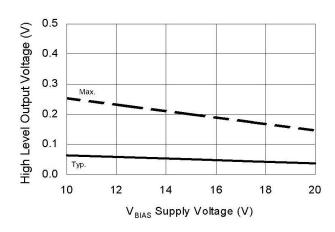


Figure 14B. High Level Output Voltage vs. Supply Voltage

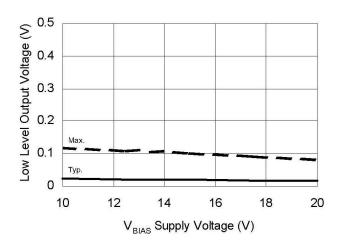


Figure 15B. Low Level Output Voltage vs. Supply Voltage

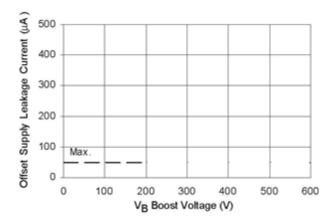
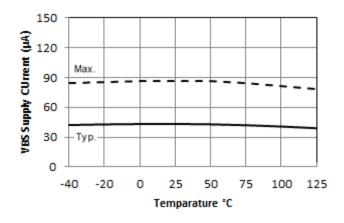


Figure 16B. Offset Supply Current vs. Voltage



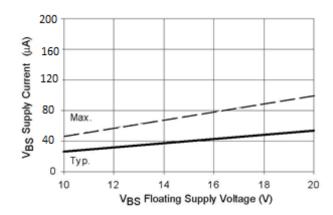
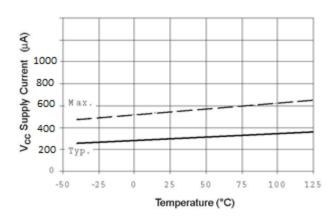


Figure 17A. V_{BS} Supply Current vs. Temperature

Figure 17B. V_{BS} Supply Current vs. Voltage



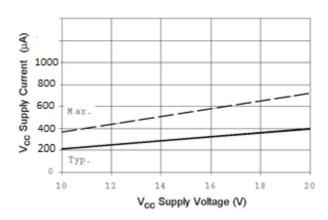
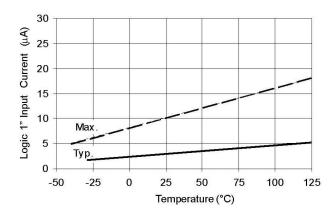


Figure 18A. V_{CC} Supply Current vs. Temperature

Figure 18B. V_{CC} Supply Current vs. Voltage



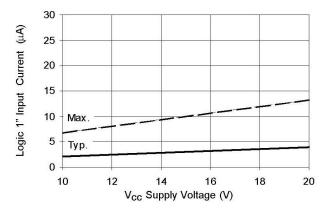


Figure 19A. Logic "1" Input Current vs. Temperature

Figure 19B. Logic "1" Input Current vs. Voltage

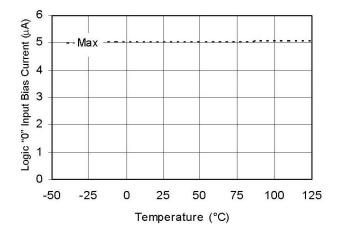
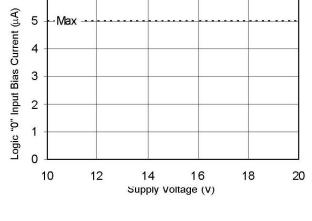


Figure 20A. Logic "0" Input Bias Current



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Figure 20B. Logic "0" Input Bias Current

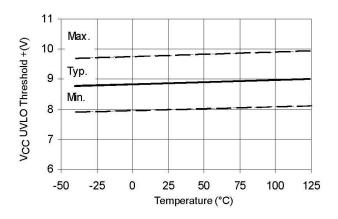


Figure 21A. $V_{CC}\V_{BS}$ Undervoltage Threshold(+) vs. Temperature

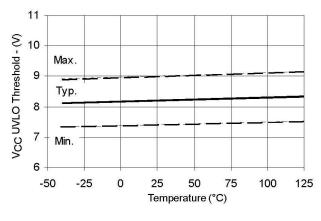


Figure 21B. V_{CC}\V_{BS} Undervoltage Threshold(-) vs. Temperature

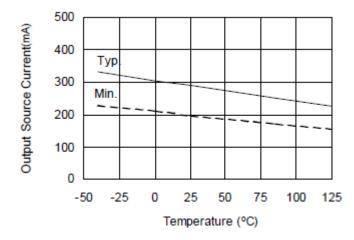


Figure 22A. Output Source Current vs. Temperature

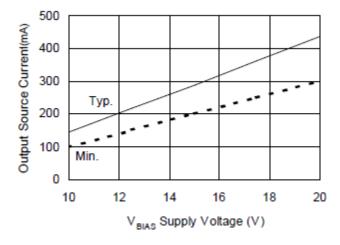
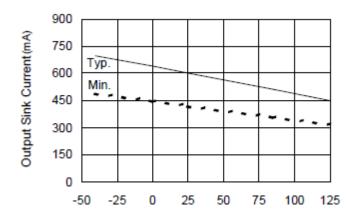


Figure 22B. Output Source Current vs. Supply Current



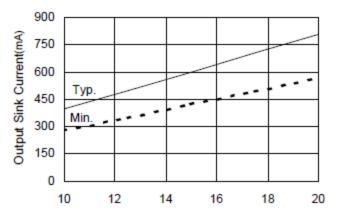
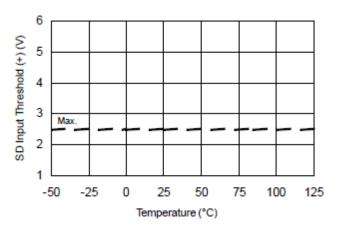


Figure 23A. Output Sink Current vs. Temperature

Figure 23B. Output Sink Current vs. Supply Voltage



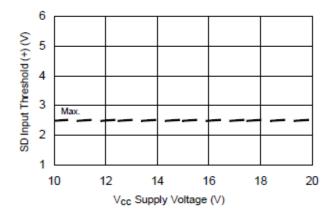
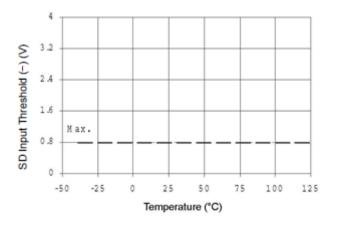


Figure 24A. SD input Positive Going Threshold(+) vs. Temperature

Figure 24B. SD input Positive Going Threshold(+) vs. Supply Voltage



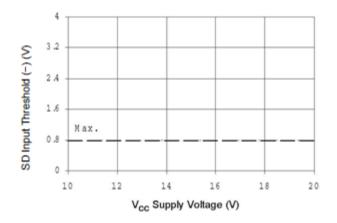
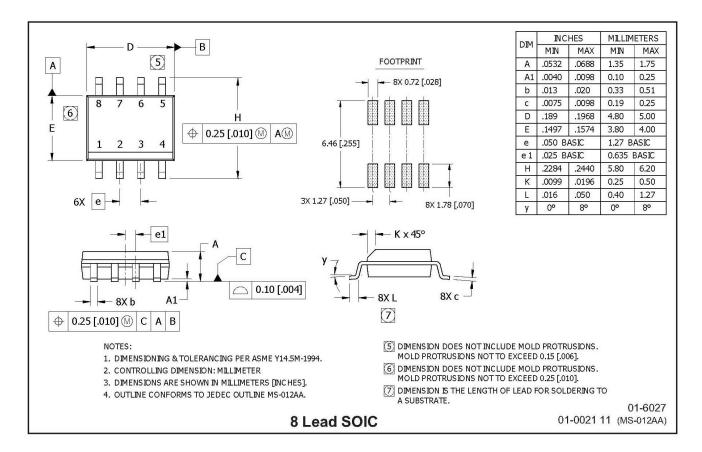


Figure 25A. SD input Negative Going Threshold(-) vs. Temperature

Figure 25A. SD input Negative Going Threshold(-) vs. Voltage

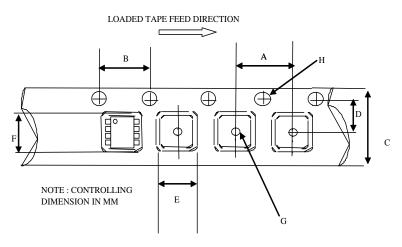


Package Details: 8-Lead SOIC



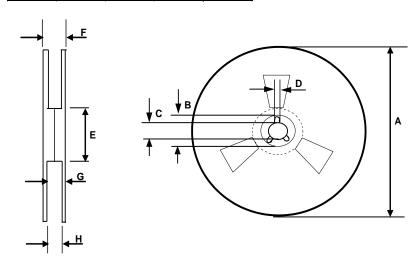


Tape and Reel Details: 8-Lead SOIC



CARRIER TAPE DIMENSION FOR 8SOICN

	Metric		Imp	erial
Code	Min	Max	Min	Max
Α	7.90	8.10	0.311	0.318
В	3.90	4.10	0.153	0.161
С	11.70	12.30	0.46	0.484
D	5.45	5.55	0.214	0.218
E	6.30	6.50	0.248	0.255
F	5.10	5.30	0.200	0.208
G	1.50	n/a	0.059	n/a
Н	1.50	1.60	0.059	0.062

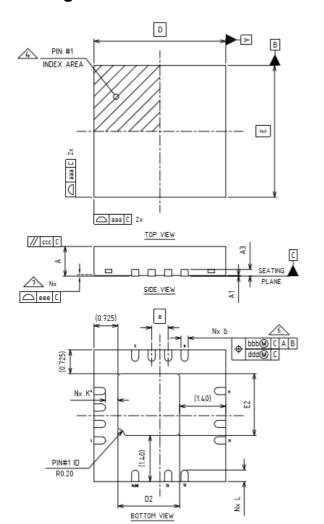


REEL DIMENSIONS FOR 8SOICN

	Metric		Imp	erial
Code	Min	Max	Min	Max
Α	329.60	330.25	12.976	13.001
B C	20.95	21.45	0.824	0.844
	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E F	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
Н	12.40	14.40	0.488	0.566



Package Details: 14-Lead MLPQ 4x4



NOTE:

- 1. Dimensioning and tolerancing conform to ASME Y14.5-2009.
- 2. All dimensions are in millimeters.
- 3. N is the total number of terminals.

4. The location of the marked terminal #1 identifier is within the hatched area.

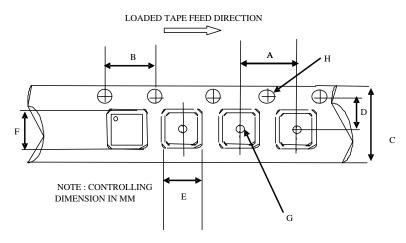
5. ND and NE refer to the number of terminals on each D and E side respectively.

Dimension b applies to the metalized terminal and is measured between 0.15mm and 0.30mm from the terminal tip. If the terminal has a radius on the other end of it, dimension b should not be measured in that radius area.

(Coplanarity applies to the terminals and all other bottom surface metalization.

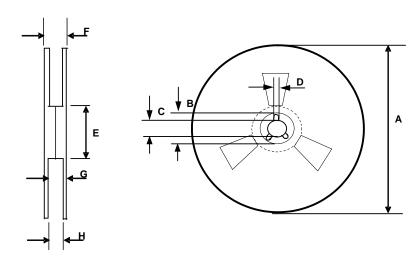
	Dimension Table					
Thickness Symbol	٧			NOTE		
mboi	MINIMUM	NOMINAL	MAXIMUM			
A	0.80	0.90	1.00			
A1	0.00	0.02	0.05			
A3		0.20 Ref				
ь	0.18	0.25	0.30	6		
D		4.00 BSC				
E		4.00 BSC				
e		0.50 BSC				
D2	1.725 1.875 1.975					
E2	1.725	1.875	1.975			
K	0.20					
L	0.25	0.35	0.45			
aaa		0.05				
bbb		0.10				
CCC		0.10				
ddd		0.05				
eee	0.08					
N	14			3		
ND	SEE FIGURE			5		
NE						
NOTES		1, 2				

Tape and Reel Details: 14-Lead MLPQ 4x4



CARRIER TAPE DIMENSION FOR MLPQ4x4

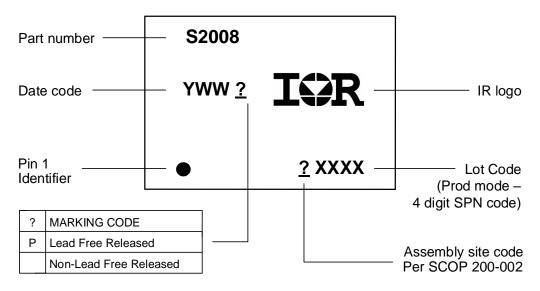
	Metric		lm	perial
Code	Min	Max	Min	Max
Α	7.90	8.10	0.311	0.358
В	3.90	4.10	0.153	0.161
С	11.70	12.30	0.461	0.484
D	5.45	5.55	0.215	0.219
E	4.25	4.45	0.168	0.176
F	4.25	4.45	0.168	0.176
G	1.50	n/a	0.069	n/a
Н	1.50	1.60	0.069	0.063



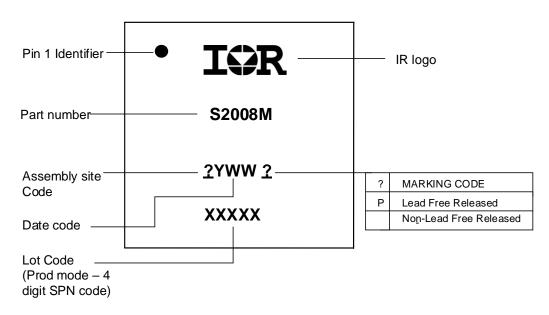
REEL DIMENSIONS FOR MLPQ4x4

	Metric		lm	perial
Code	Min	Max	Min	Max
Α	329.60	330.25	12.976	13.001
В	20.95	21.45	0.824	0.844
С	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
Е	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
Н	12.40	14.40	0.488	0.566

Part Marking Information



8-Lead SOIC8 IRS2008SPBF



14-Lead MLPQ 4x4 IRS2008MPBF



Qualification Information[†]

Qualification information				
Qualification Level			Industrial [†]	
		tests of JEDEC47/22/20.	Comments: This family of ICs is qualified according to relevant tests of JEDEC47/22/20. IR's Consumer qualification level is granted by extension of the higher Industrial level.	
Moisture Sensitivity Level		8 Lead SOIC	MSL2 ^{††} , 260°C (per IPC/JEDEC J-STD-020)	
		14-Lead MLPQ 4x4		
ESD	Human Body Model	Class 2		
		(per JEDEC standard JESD22-A114)		
	Machine Model		Class A	
		(per EIA/JEDEC standard EIA/JESD22-A115)		
IC Latch-Up Test			Class I	
			(per JESD78)	
RoHS Compliant			Yes	

According to IR Qualification Requirements for IC products.

[†] †† Higher MSL ratings may be available for the specific package types listed here. Please contact your Infineon sales representative for further information.



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